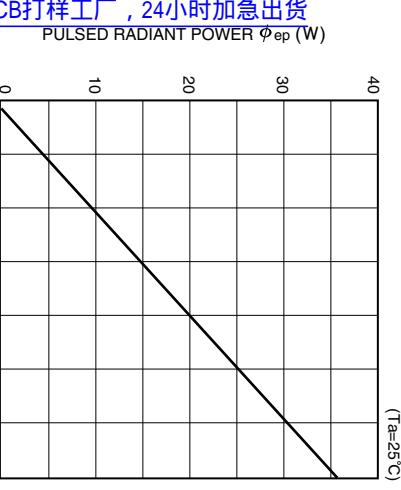


HIGH-POWER INFRARED PULSED LASER DIODE L7060-02

Figure 2: Typical Radiant Power vs. Pulsed Forward Current



捷多邦, 专业PCB打样工厂, 24小时加急出货

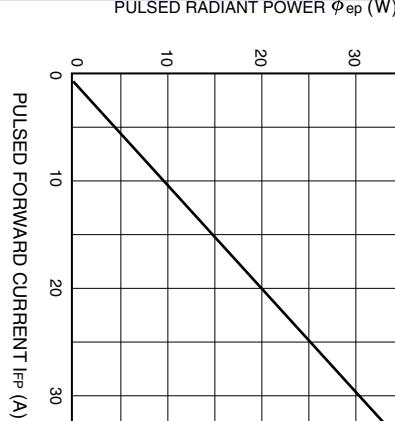
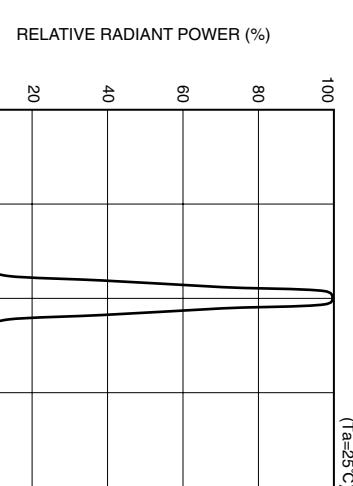


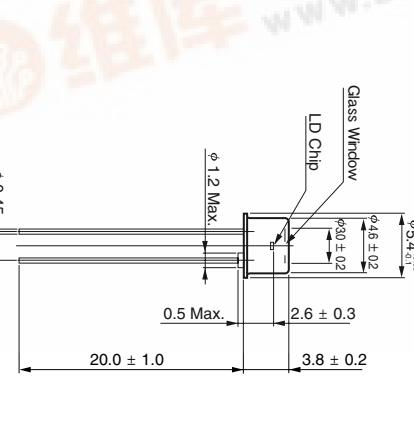
Figure 4: Typical Directivity

Figure 3: Typical Emission Spectrum



- **APPLICATIONS**
- Laser rader
- Range finder
- Excitation light source
- Optical trigger
- Security barrier

Figure 1: Dimensional Outline (Unit: mm)



■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Pulsed Forward Current	Ifp	35	A			
Reverse Voltage	Vr	2	V			
Pulsed Radiant Output Power	phi_ep	40	W			
Pulse Duration (FWHM)	tw	100	ns			
Duty Ratio	DR	0.075	%			
Operating Temperature	T_top	-30 to +85	°C			
Storage Temperature	T_stg	-40 to +125	°C			

Handling Precautions for L7060-02

The LD (laser diode) may be damaged or its performance may deteriorate due to such factors as electrostatic discharge from the human body, surge voltages from measurement equipment, leakage voltages from soldering irons, and packing materials. As a countermeasure against static electricity, the device, operator, work place and measuring jigs must all be set at the same electric potential. In using LD, observe the following precautions:

- To protect the device from static electricity charges which accumulate on the operator or the operator's clothes, use a wrist strap etc. to ground the operator's body via a high impedance resistor (1MΩ).
- A semiconductive sheet should be laid on both the work table and the floor in the work area. When soldering, use an electrically grounded soldering iron with an isolation resistance of more than 10MΩ.
- For containers for transportation and packing, use of antistatic material (material that minimizes the generation of static charge when rubbed against or separated from itself or other similar materials).

2. Precautions for mounting
 (1) Lead forming
 To form the leads, hold the base of the leads securely and bend them so that no force is applied to the package. Lead forming should be done before soldering.

3. Precautions for handling
 If leads are out when still at a high temperature, this may cause an electrical discontinuity. Always cut off the leads when they are at room temperature. Never cut off the leads immediately after they are soldered.

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HAMAMATSU
HIGH-POWER INFRARED PULSED LASER DIODE
L7060-02

Note: General operating condition $\phi_{ep} \leq 30$ W, $t_w \leq 50$ ns, Repetition frequency ≤ 8 kHz
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HIGH-POWER INFRARED PULSED LASER DIODE L7060-02

Figure 3: Typical Emission Spectrum

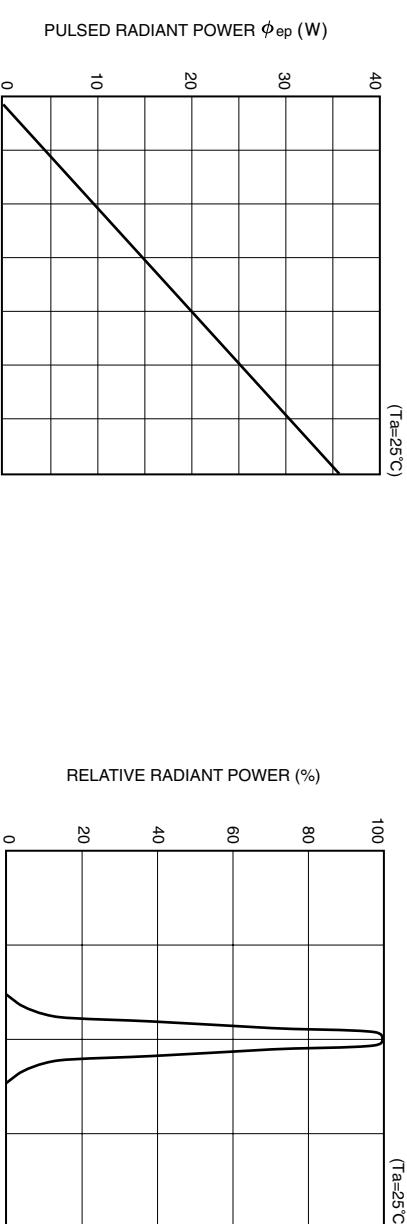
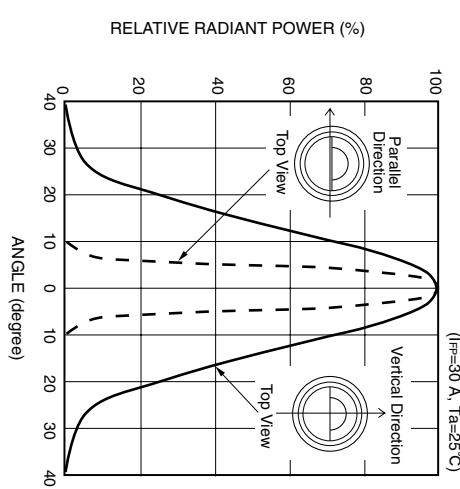


Figure 4: Typical Directivity



Handling Precautions for L7060-02

The LD (laser diode) may be damaged or its performance may deteriorate due to such factors as electrostatic discharge from the human body, surge voltages from measurement equipment, leakage voltages from soldering irons, and packing materials. As a countermeasure against static electricity, the device, operator, work place and measuring jigs must all be set at the same electric potential. In using LD, observe the following precautions:

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- For containers for transportation and packing, use of antistatic material (material that minimizes the generation of static charge when rubbed against or separated from itself or other similar materials).

Precautions for mounting

- (1) Lead forming

To form the leads, hold the base of the leads securely and bend them so that no force is applied to the package. Lead forming should be done before soldering.
- (2) Cutting off the leads

If leads are out when still at a high temperature, this may cause an electrical discontinuity. Always cut off the leads when they are at room temperature. Never cut off the leads immediately after they are soldered.

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HIGH-POWER INFRARED PULSED LASER DIODE L7060-02

HIGH-POWER INFRARED PULSED LASER DIODE L7060-02

- FEATURES**
 - High output power ($\phi_{ep} \geq 30W$)
 - High speed rise time ($tr=0.5$ ns typ.)

- APPLICATIONS**
 - Laser rader
 - Range finder
 - Excitation light source
 - Optical trigger
 - Security barrier

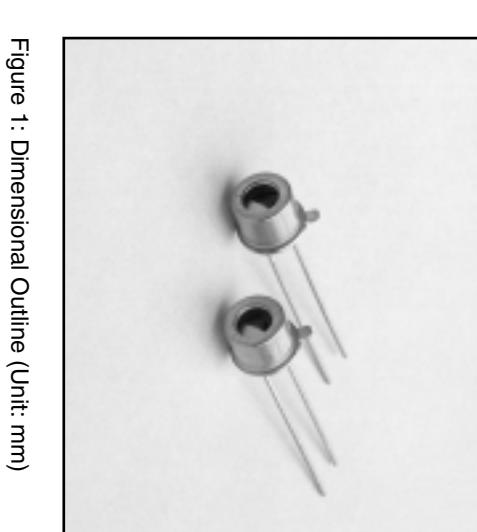


Figure 1: Dimensional Outline (Unit: mm)

■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Pulsed Forward Current	Ifp	Ifp=30A	30	-	-	W
Reverse Voltage	V _R		2	V		
Pulsed Radiant Output Power	ϕ_{ep}		40	W		
Pulse Duration (FWHM)	t _w		100	ns		
Duty Ratio	DR		0.075	%		
Operating Temperature	T _{op}	-30 to +85		°C		
Storage Temperature	T _{stg}	-40 to +125		°C		

■ ELECTRICAL AND OPTICAL CHARACTERISTICS (Ta=25°C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Pulsed Radiant Power	ϕ_{ep}	Ifp=30A	30	-	-	W
Peak Emission Wavelength	λ_p		-	870	-	nm
Spectral Radiation Half Bandwidth	$\Delta \lambda$		-	4	-	nm
Forward Voltage	V _F	Ifp=30A	-	7	-	V
Rise Time	t _r		-	0.5	-	ns
Beam Spread Angle : Parallel	$\theta //$		-	9	-	deg
Lasing Threshold Current	I _{th}	Ifp=30A	-	30	-	deg

Note: General operating condition $\phi_{ep} \leq 30$ W, $t_w \leq 50$ ns, Repetition frequency ≤ 8 kHz

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